

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	$0.53m\Omega@10V$	570A



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

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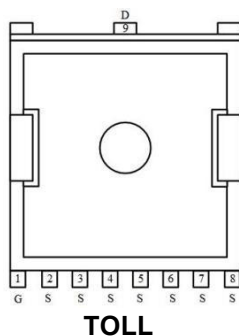
Feature

- Fast Switching
- Low Gate Charge and $R_{DS(on)}$
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

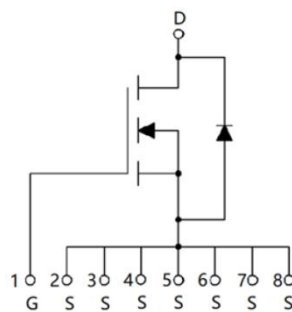
Applications

- Power switching application
- DC-DC Converter
- Power Management

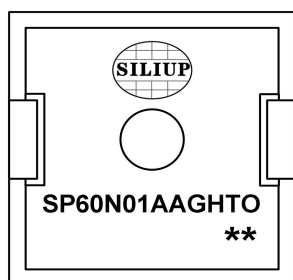
Package



Circuit diagram



Marking



SP60N01AAGHTO : Product code
****** : Week code

Order Information

Device	Package	Unit/Tape
SP60N01AAGHTO	TOLL	2000

Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	570	A
Continuous Drain Current (Tc=100°C)	I_D	380	A
Pulsed Drain Current	I_{DM}	2280	A
Single Pulse Avalanche Energy ¹	E_{AS}	2570	mJ
Power Dissipation (Tc=25°C)	P_D	415	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	0.30	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

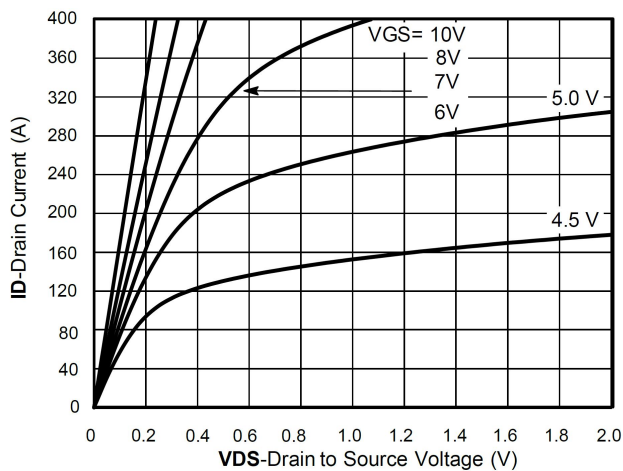
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	60	-	-	V
Drain-Source Leakage Current	IDSS	VDS=48V , VGS=0V	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	2.0	3.0	4.0	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=30A	-	0.53	0.68	mΩ
Dynamic characteristics						
Input Capacitance	Ciss	VDS=30V , VGS=0V , f=1MHz	-	16126	-	pF
Output Capacitance	Coss		-	8027	-	
Reverse Transfer Capacitance	Crss		-	799	-	
Total Gate Charge	Qg	VDS=30V , VGS=10V , ID=50A	-	280	-	nC
Gate-Source Charge	Qgs		-	85	-	
Gate-Drain Charge	Qgd		-	48	-	
Switching Characteristics						
Turn-On Delay Time	Td(on)	VDD=30V , VGS=10V , RG=2.7Ω , ID=50A	-	35	-	nS
Rise Time	Tr		-	95	-	
Turn-Off Delay Time	Td(off)		-	229	-	
Fall Time	Tf		-	158	-	
Diode Characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	IS		-	-	570	A
Reverse Recovery Time	Trr	IS=50A , di/dt=100A/us , TJ=25℃	-	229	-	nS
Reverse Recovery Charge	Qrr		-	480	-	nC

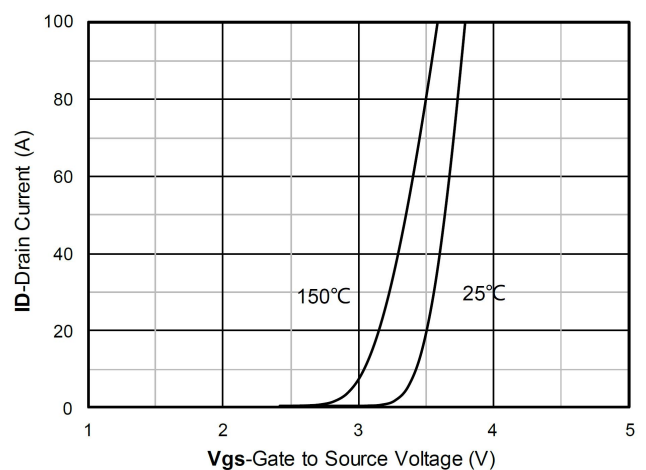
Note :

1. The test condition is $V_{DD}=30V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

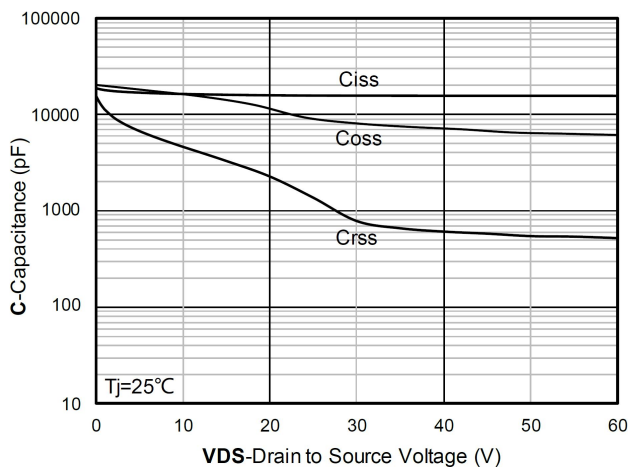
Typical Characteristics



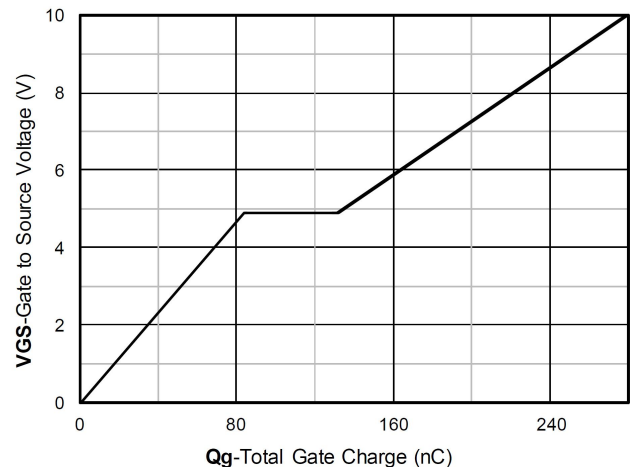
Output Characteristics



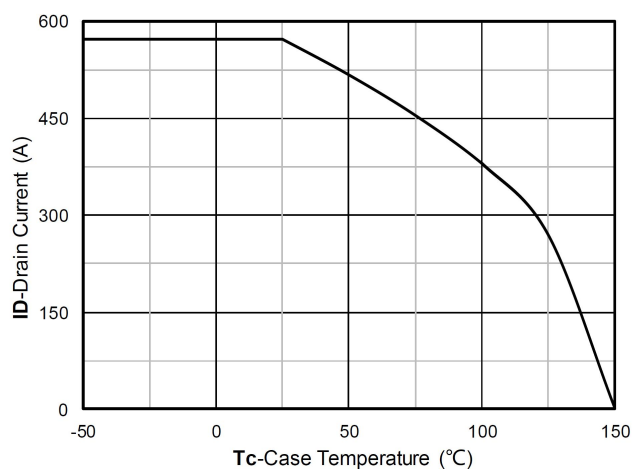
Transfer Characteristics



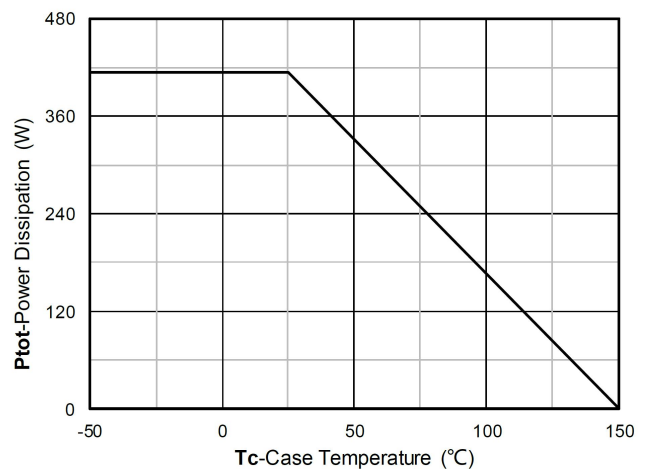
Capacitance Characteristics



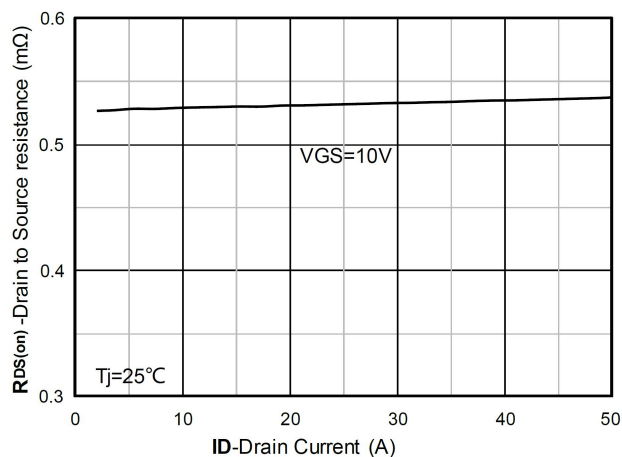
Gate Charge



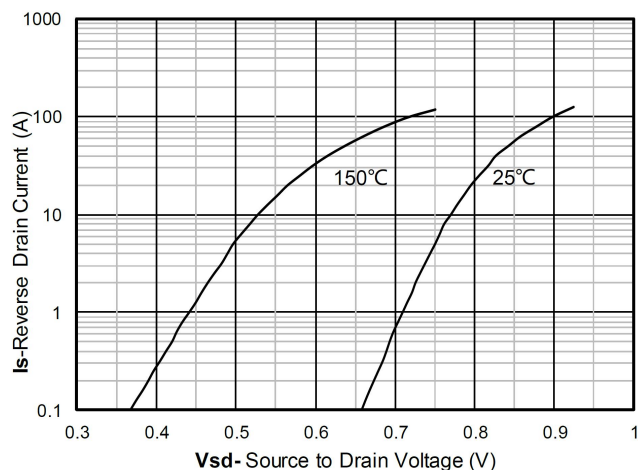
Current dissipation



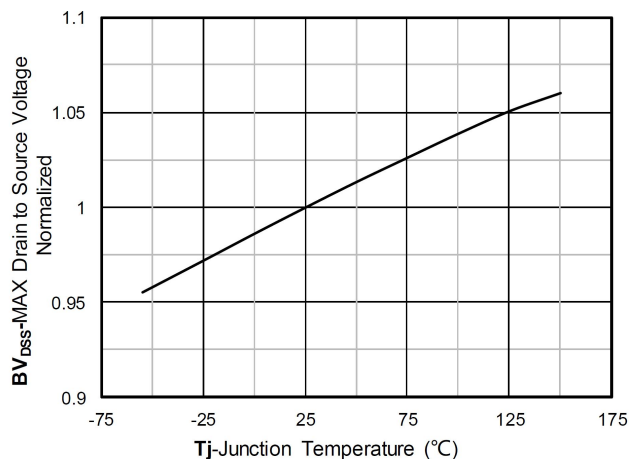
Power dissipation



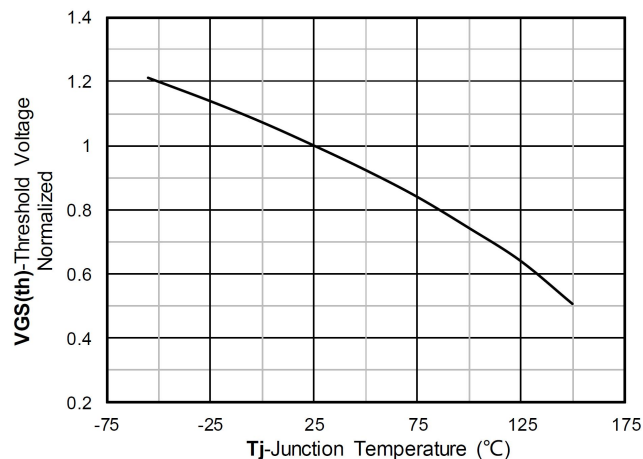
RDS(on) VS Drain Current



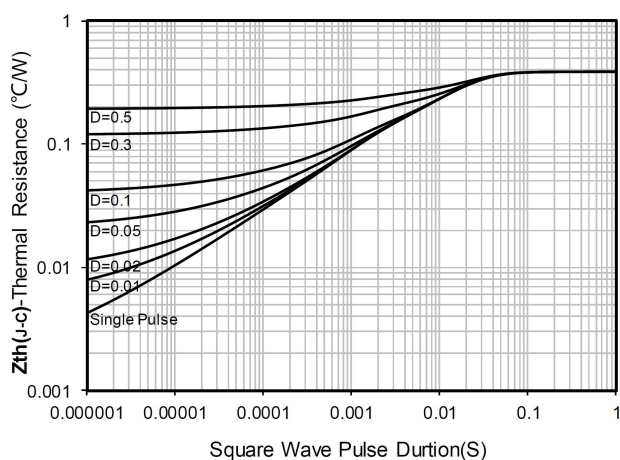
Forward characteristics of reverse diode



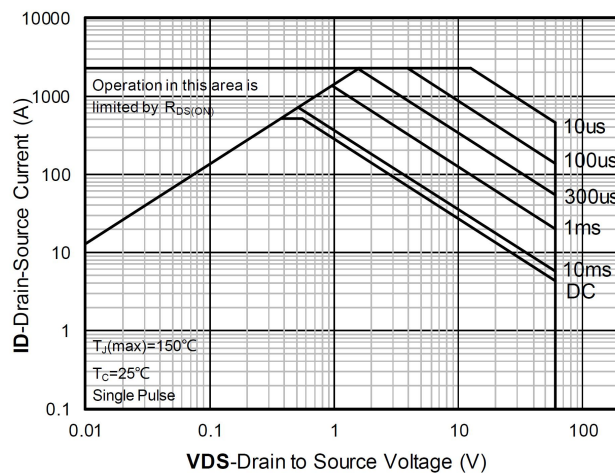
Normalized breakdown voltage



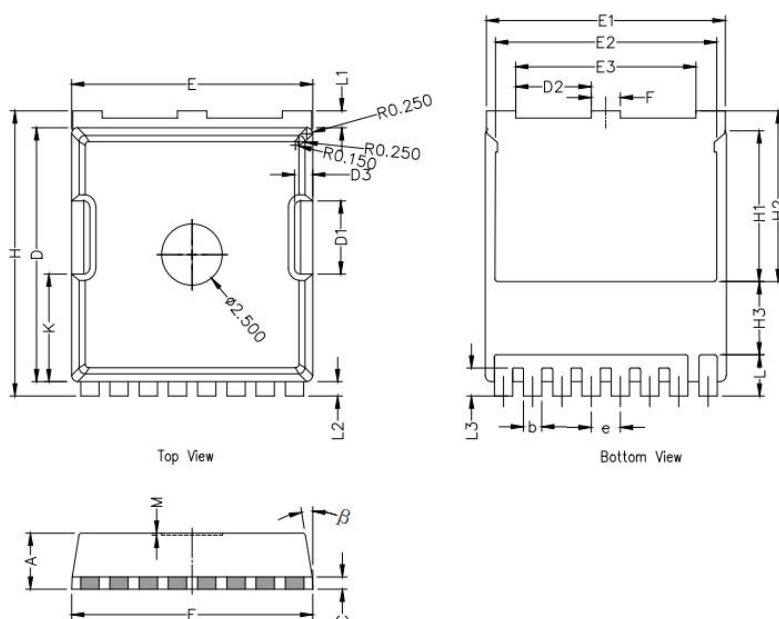
Normalized Threshold voltage



Maximum Transient Thermal Impedance



Safe Operation Area

TOLL Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.7	0.85
L2	0.45	0.6	0.75
M	0.08 REF.		
β	8°	10°	12°
K	4.25	4.40	4.55